• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

■AEC-Q101 Qualified

■Low $R_{DS(ON)}$ to minimize conductive loss

■Low Gate Charge for fast switching

■Low Thermal resistance

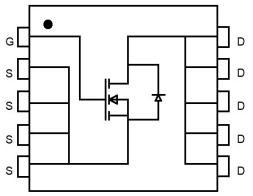
•Application

■BLDC Motor driver

■DC-DC

■Load Switch

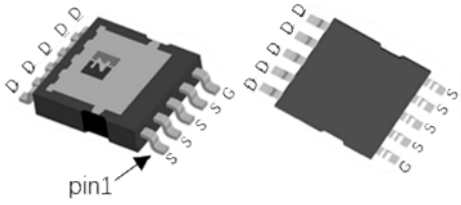
• Product Summary



V_{DS}= 40V

$R_{DS(ON)}$ = 2.2mΩ

I_D= 135A



TCPAK5x7

RoHS

REACH COMPLIANT

HF

•Ordering Information:

Part NO.	ZMSA022N04HTNC
Marking	22N04H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

•Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage	V_{GS}		±20	V
Continuous Drain Current	I_D	T_C=25℃	135	A
	I_D	T_C=75℃	111	A
	I_D	T_C=100℃	96	A
Pulsed Drain Current ①	I_{DM}	Pulsed; t_p ≤ 10 μs; T_{mb} = 25 °C;	540	A
Total Power Dissipation	P_D	T_C=25℃	107	W
Total Power Dissipation	P_D	T_A=25℃	5.0	W
Operating Junction Temperature	T_J		-55 to +175	℃
Storage Temperature	T_{STG}		-55 to +175	℃
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, VGS=10V, Rg=25Ω,	106	mJ
		L=0.5mH, VGS=10V, Rg=25Ω,	190	mJ
ESD Level (HBM)	CLASS 2			

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	1.4	°C/W
Thermal resistance, junction-ambient	$R_{thJA①}$		-	30	°C/W
Soldering temperature（total time<10s)	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250uA	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	2	2.9	4	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}= 40V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} = 0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D= 30A		2.2	2.9	mΩ
Forward Transconductance	g_{FS}	V_{GS} =5V, I_{SD} = 5A		20		S
Diode Forward Voltage	V_{FSD}	V_{GS} =0V, I_{SD} = 30A			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V_{DS}=25V	-	1773	-	pF
Output capacitance	Coss		-	567	-	
Reverse transfer capacitance	Crss		-	35	-	
Gate Risistance	Rg	f = 1MHz	-	1.9		Ω
Total gate charge	Qg	V_{DD} = 15V, I_D = 24A, V_{GS} = 10V	-	26.5	-	nC
Gate - Source charge	Qgs		-	7.8	-	
Gate - Drain charge	Qgd		-	6.2	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V,V_{DS}=15V, R_G =3.3Ω, I_D =20A	-	12	-	ns
Turn-ON Rise time	t_r		-	50	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	25	-	ns
Turn-Off Fall time	t_f		-	6	-	ns
Reverse Recovery Time	t_{rr}	V_{DD}=20V, dI_S/dt = 100A/us, I_S=20A	-	49	-	ns
Reverse Recovery Charge	Q_{rr}		-	48	-	nC

Fig.1 Gate-Charge Characteristics

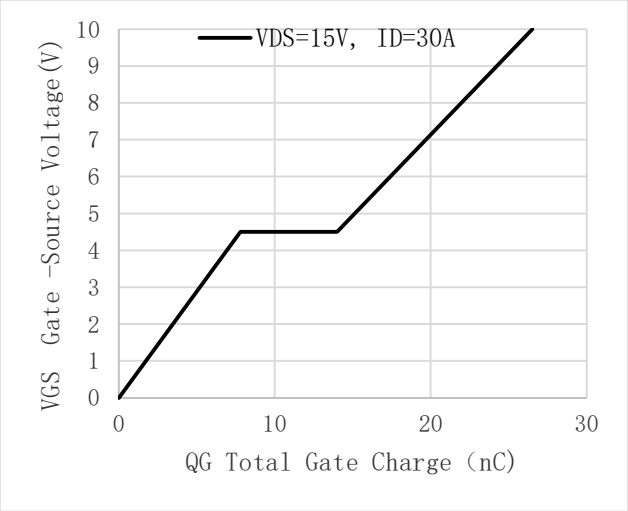


Fig.2 Capacitance Characteristics

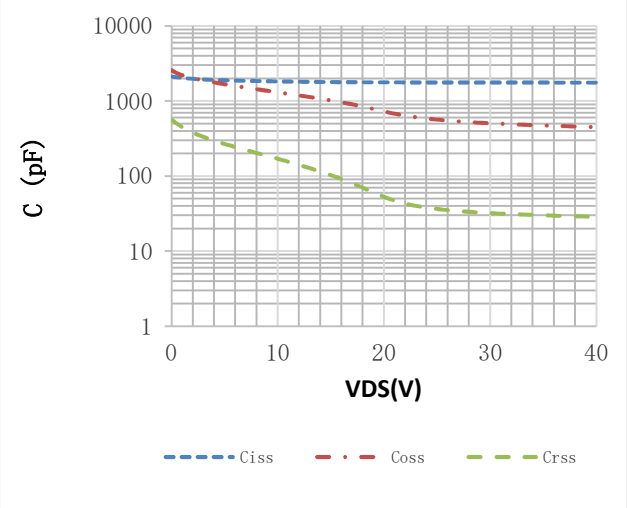


Fig.3 Power Dissipation

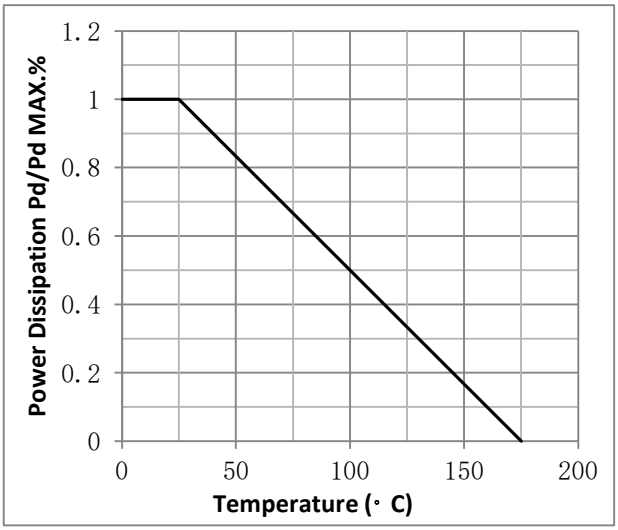


Fig.4 Typical output Characteristics

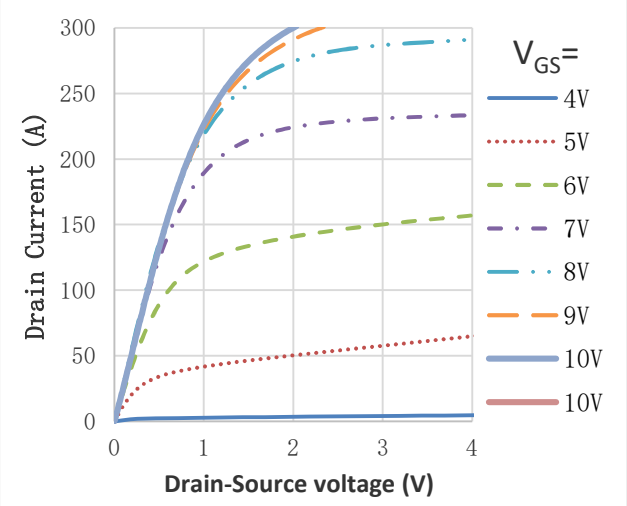


Fig.5 Threshold Voltage V.S Junction Temperature

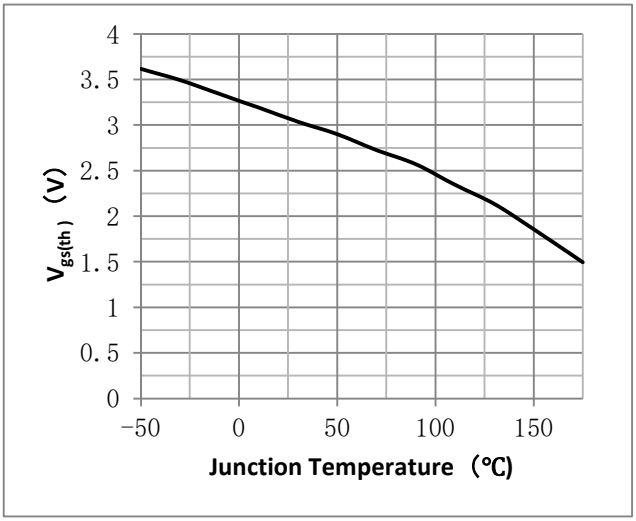


Fig.6 Resistance V.S Drain Current

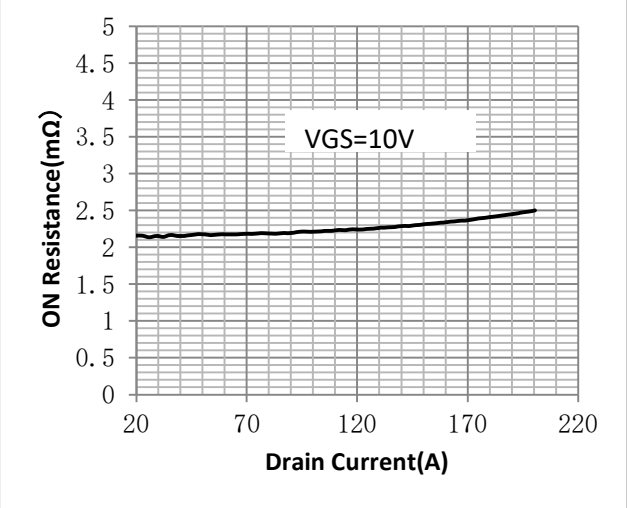


Fig.7 On-Resistance VS Gate Source Voltage

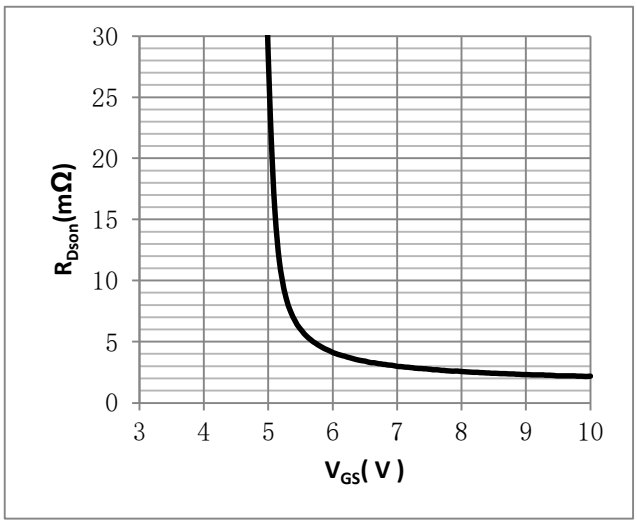


Fig.8 On-Resistance V.S Junction Temperature

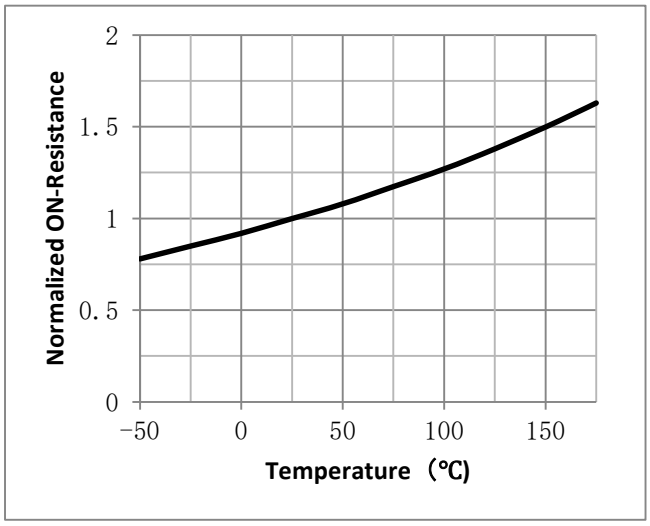


Figure 9. Diode Forward Voltage vs. Current

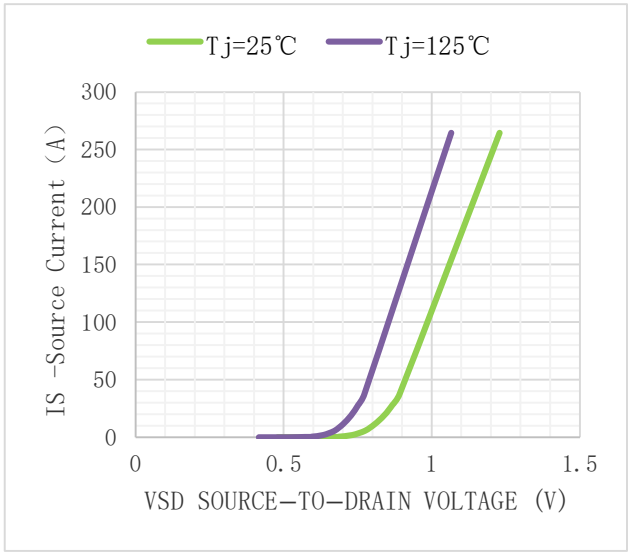


Figure 10. Transfer Characteristics

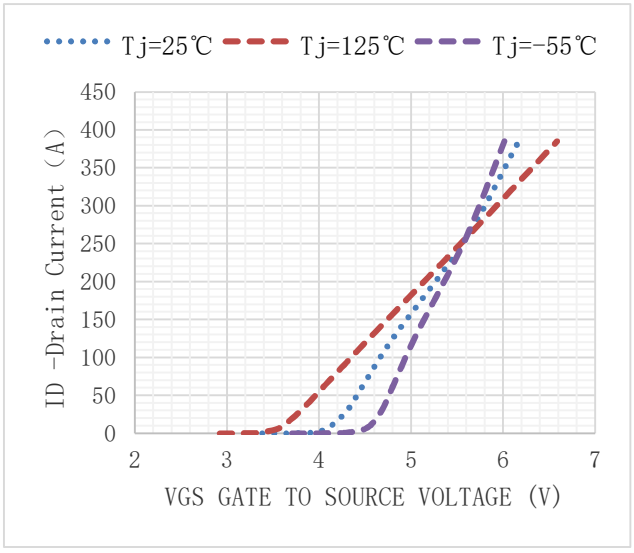


Fig.11 SOA Maximum Safe Operating Area

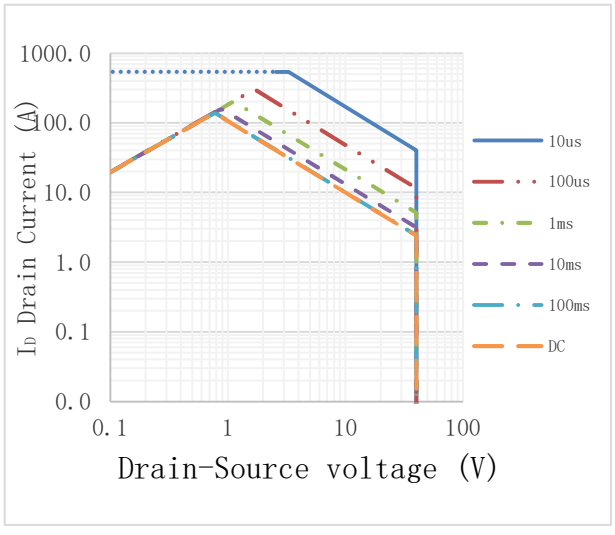
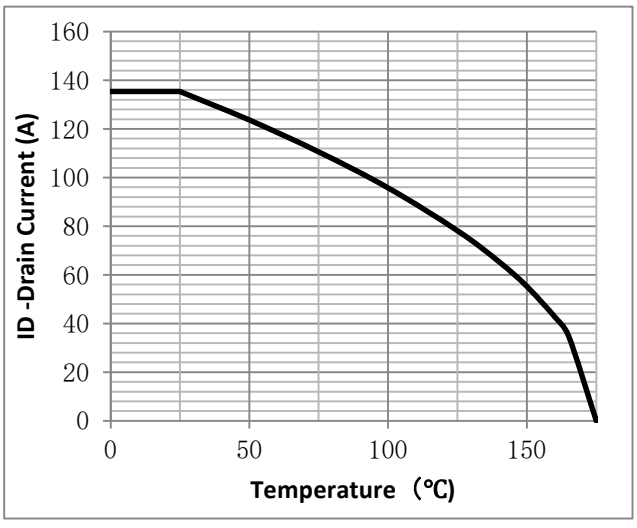
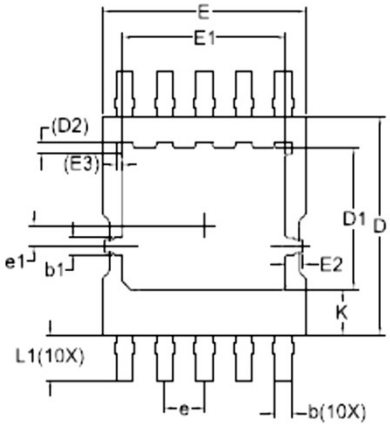


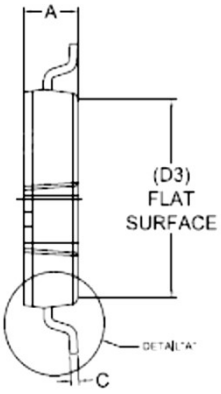
Fig.12 ID vs. Junction Temperature②



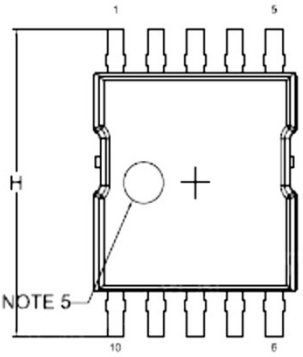
●TCPAK5x7 Package Outline



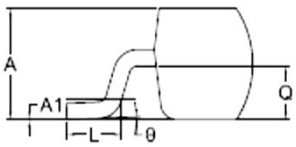
TOP VIEW



SIDE VIEW



BOTTOM VIEW



DEDAIL"A"
(2:1)

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1,25	1,35	1,45
A1	-0.05	0	0.075
b	0.36	0.41	0.46
b1	0.30	0.40	0.50
c	0,16	0,20	0,26
D	5,20	5,30	5,40
D1	3.35	3.45	3.55
D2	0,29 REF		
D3	4,82 REF		
E	5,00	5,10	5,20
E1	4.02	4.12	4.22
E2	0.30	0.44	0.50
E3	0,14 REF		
e	1,00 BSC		
e1	0,50 BSC		
K	1.00	1.10	1.20
H	7,30	7,50	7,70
L	0,49	0,69	0,89
L1	0,90	1,10	1,30
Q	0,60	0,65	0,70
θ	0°	2.5°	5°

Note:

① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

②Practically the current will be limited by PCB, thermal design and operating temperature. V_{GS}=10V.

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Revision History

Version	Date	Change
A	2024/8/26	New